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With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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SMALL SIGNAL NPN TRANSISTORS

PRELIMINARY DATA

Туре	Marking		
BC847B	1F		
BC847C	1G		

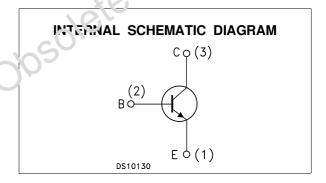
- SILICON EPITAXIAL PLANAR NPN TRANSISTORS
- MINIATURE SOT-23 PLASTIC PACKAGE FOR SURFACE MOUNTING CIRCUITS
- TAPE AND REEL PACKING
- BC847B THE PNP COMPLEMENTARY TYPE IS BC857B

APPLICATIONS

- WELL SUITABLE FOR PORTABLE EQUIPMENT
- SMALL LOAD SWITCH TRANSISTORS WITH HIGH GAIN AND LOW SATURATION VOLTAGE

Producils





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
Усво	Collector-Base Voltage (I _E = 0)	50	V
VCEO	Collector-Emitter Voltage (I _B = 0)	45	٧
V_{EBO}	Emitter-Base Voltage (I _C = 0)	6	٧
Ic	Collector Current	100	mA
I _{CM}	Collector Peak Current	200	mA
P _{tot}	Total Dissipation at T _C = 25 °C	250	mW
T _{stg}	Storage Temperature	-65 to 150	°C
Tj	Max. Operating Junction Temperature	150	°C

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THERMAL DATA

R _{thj-amb} •	Thermal Resistance Junction-Ambient	Max	500	°C/W	
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[•] Device mounted on a PCB area of 1 cm².

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

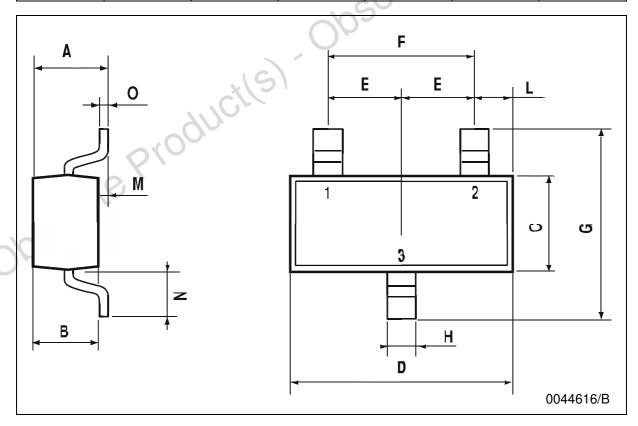
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
I _{CBO}	Collector Cut-off Current (I _E = 0)	$V_{CB} = 30 \text{ V}$ $V_{CB} = 30 \text{ V}$ $T_{C} = 150 ^{\circ}\text{C}$			15 5	nΑ μΑ
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 5 V			100	nA
V _{(BR)CBO}	Collector-Base Breakdown Voltage (I _E = 0)	I _C = 10 μA	50			V
V _{(BR)CEO*}	Collector-Emitter Breakdown Voltage (I _B = 0)	I _C = 2 mA	45			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage (I _C = 0)	$I_E = 10 \mu A$	6		Cil) v
$V_{CE(sat)^*}$	Collector-Emitter Saturation Voltage	$\begin{array}{cccccccccccccccccccccccccccccccccccc$		0.09 0.2	0.25 0.6	V V
V _{BE(sat)*}	Base-Emitter Saturation Voltage	$I_{C} = 10 \text{ mA}$ $I_{B} = 0.5 \text{ mA}$ $I_{C} = 100 \text{ mA}$ $I_{B} = 5 \text{ mA}$. 7	0.7 0.9		V V
V _{BE(on)} *	Base-Emitter On Voltage	I _C = 2 mA	0.58	0.66	0.7 0.77	V V
h _{FE} *	DC Current Gain	$I_{C} = 10 \ \mu A$ for BC847B for BC847C $I_{C} = 2 \ mA$ for BC847B for BC847C	200 420	150 270 290 520	450 800	
f _T	Transition Frequency	I _C = 10 mA V _{CE} = 5 V f = 100MHz	100			MHz
Ссво	Collector-Base Capacitance	I _E = 0 V _{CB} = 10 V f = 1 MHz		2.5		pF
NF	Noise Figure	V_{CE} = 5 V I_{C} = 0.2 mA f = 1KHz Δf = 200 Hz R_{G} = 2 K Ω		2	10	dB

^{*} Pulsed: Pulse duration = 300 μs, duty cycle ≤ 2 %

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SOT-23 MECHANICAL DATA

DIM.	mm			mils		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	0.85		1.1	33.4		43.3
В	0.65		0.95	25.6		37.4
С	1.20		1.4	47.2		55.1
D	2.80		3	110.2		118
Е	0.95		1.05	37.4		41.3
F	1.9		2.05	74.8		80.7
G	2.1		2.5	82.6		98.4
Н	0.38		0.48	14.9		18.8
L	0.3		0.6	11.8	100/0	23.6
М	0		0.1	0	510	3.9
N	0.3		0.65	11.8		25.6
0	0.09		0.17	3.5		6.7



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